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List of Publications by Year in descending order

28 papers	1,158 citations	687363 13 h-index	526287 27 g-index
28 all docs	28 docs citations	28 times ranked	1001 citing authors

#	Article	IF	Citations
1	Nature of the 2.8 eV photoluminescence band in Mg doped GaN. Applied Physics Letters, 1998, 72, 1326-1328.	3.3	342
2	Origin of defect-related photoluminescence bands in doped and nominally undoped GaN. Physical Review B, 1999, 59, 5561-5567.	3.2	260
3	Ionized donor bound excitons in GaN. Applied Physics Letters, 1997, 71, 1837-1839.	3.3	66
4	Electrical conductivity in mixed-alkali iron phosphate glasses. Journal of Non-Crystalline Solids, 2001, 283, 119-128.	3.1	58
5	Thermoelectric effect spectroscopy of deep levelsâ€”application to semiâ€insulating GaAs. Applied Physics Letters, 1990, 56, 2636-2638.	3.3	55
6	The dc electrical conductivity of iron phosphate glasses. Journal of Non-Crystalline Solids, 2001, 296, 65-73.	3.1	55
7	On the hole effective mass and the free hole statistics in wurtzite GaN. Semiconductor Science and Technology, 2003, 18, 219-224.	2.0	52
8	Electrical relaxation in mixed alkali iron pyrophosphate glasses. Journal of Non-Crystalline Solids, 2000, 263-264, 299-304.	3.1	38
9	Optically enhanced photoconductivity in semiâ€insulating gallium arsenide. Applied Physics Letters, 1989, 54, 810-812.	3.3	34
10	EL2 related deep traps in semiâ€insulating GaAs. Applied Physics Letters, 1991, 58, 278-280.	3.3	34
11	Trapâ€induced photoconductivity in semiâ€insulating GaAs. Journal of Applied Physics, 1990, 67, 1408-1411.	2.5	26
12	Crystal data for CuGaxIn1â^'xTe2. Journal of Applied Crystallography, 1983, 16, 576-576.	4.5	21
13	Quenching and enhancement of photoconductivity in semi-insulating GaAs. Solid State Communications, 1990, 74, 847-850.	1.9	14
14	Light-intensity dependence of slow-relaxation phenomena in semi-insulating GaAs. Applied Physics A: Solids and Surfaces, 1990, 51, 379-381.	1.4	13
15	Measurement of the refractive index and thickness of a transparent film from the shift of the interference pattern due to the sample rotation. Thin Solid Films, 2010, 518, 3619-3624.	1.8	13
16	Electrical Properties of CuGaxIn1â^'xTe2 Semiconductors. Physica Status Solidi A, 1992, 133, 137-146.	1.7	10
17	A comparative study of deep levels in undoped semi-insulating gallium arsenide wafers using thermally stimulated current spectra. Journal Physics D: Applied Physics, 1995, 28, 934-938.	2.8	10
18	On the evaluation of optical parameters of a thin semiconductor film from transmission spectra, and application to GaN films. Measurement Science and Technology, 2008, 19, 105303.	2.6	8

#	Article	IF	Citations
19	Photoconductivity transients and photosensitization phenomena in semiâ€insulating GaAs. Journal of Applied Physics, 1993, 73, 5181-5184.	2.5	7
20	Calculation of the glow curve shape â€" application to the thermally stimulated currents (TSC). Solid State Communications, 1991, 79, 535-538.	1.9	6
21	The analysis of low-temperature photoconductivity evolution in semi-insulating GaAs. Journal of Physics Condensed Matter, 1991, 3, 5817-5824.	1.8	6
22	Trapping and recombination processes via deep level T3 in semi-insulating gallium arsenide. Journal of Electronic Materials, 1993, 22, 403-407.	2.2	6
23	On the determination of the statistical characteristics of the magnesium acceptor in GaN. Superlattices and Microstructures, 2004, 36, 445-453.	3.1	6
24	Optical cross section for theEL2â†'EL2*metastable transformation. Physical Review B, 1995, 51, 11117-11119.	3.2	5
25	Statistics of the Mg acceptor in GaN in the band model. Semiconductor Science and Technology, 2006, 21, 1484-1487.	2.0	5
26	A simple method for determination of the Hall constant. Journal of Physics E: Scientific Instruments, 1989, 22, 997-1000.	0.7	4
27	The impact of deep levels on the photocurrent transients in semi-insulating GaAs. Journal of Electronic Materials, 2003, 32, 1100-1106.	2.2	4
28	Analysis of transient phenomena in GaAs within the metastable model. Physica Status Solidi (B): Basic Research, 1996, 195, 465-474.	1.5	0